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U AD-A239 17 25. €	_	1	N/AVAILABILITY C for public r		distribution
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6a. NAME OF PERFORMING ORGANIZATION Department of Chemistry Duke University	6b. OFFICE SYMBOL (If applicable)		ONITORING ORGA Naval Rese		
6c ADDRESS (City, State, and ZIP Code) Durham, NC 27706		300 North	ity, State, and ZIP n Quincy Str n, VA 22217	eet	
8a. NAME OF FUNDING SPONSORING ORGANIZATION Office of Naval Research	8b. OFFICE SYMBOL (If applicable)		IT INSTRUMENT ID J-1545; R&T		
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800 North Quincy Street Arlington, VA 22217-5000		PROGRAM ELEMENT NO. NR	PROJECT NO. 053	TASK NO.	WORK UNIT ACCESSION NO.
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16 SUPPLEMENTARY NOTATION Accepted for publication in	Organometallics	S.			
17 COSATI CODES FIELD GROUP SUB-GROUP	18. SUBJECT TERMS (indium-phosph ring compound	orus, synthe			
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Synthesis and Structural Characterization of Organoindium-Phosphorus Complexes Containing

a Four-Membered In-P-In-Cl or In-P-In-P Ring:

Crystal Structures of

 $(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl \ and \\ [(Me_3SiCH_2)_2InP(SiMe_3)_2]_2$

Richard L. Wells*, Andrew T. McPhail, and Mark F. Self

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ABSTRACT

The first example of an In-P-In-Cl ring containing compound, $(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl$ (1) was prepared by the reaction of $(Me_3SiCH_2)_2InCl$ and $(Me_3Si)_3P$ in a 2:1 mole ratio. Similarly, the dimer containing an In-P-In-P core, $[(Me_3SiCH_2)_2InP(SiMe_3)_2]_2$ (2) was prepared by reaction in a 1:1 mole ratio. X-ray crystallographic analyses showed the In-P-In-Cl ring of 1 to be nonplanar while the In-P-In-P ring of 2 is planar. Compound 1 belongs to the triclinic system, space group PI (Ci^I), with two molecules in a unit cell of dimensions: a = 12.581(1), b = 19.470(2), c = 9.643(1) Å, a = 89.75(1), b = 112.91(1), $g = 100.68(1)^\circ$. Compound 2 crystallizes in the orthorhombic system, space group $Pbcn(D_2h^{IA})$, with four molecules in a unit cell of dimensions: a = 12.782(2), b = 21.482(3), c = 18.651(3) Å. Compound 2 reacts with two equivalents of $(Me_3SiCH_2)_2InCl$ to yield 1 as a major product, as evidenced by ${}^{I}H$ and ${}^{I}_3C({}^{I}H)$ NMR and melting point data.

[Originally submitted to Organometallics; May 6, 1991] [Revised submitted June 20, 1991]

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[(Me₃SiCH₂)₂InP(SiMe₃)₂]₂

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(Received, 1991)

The first example of an In-P-In-Cl ring containing compound, $(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl$ (1) was prepared by the reaction of $(Me_3SiCH_2)_2InCl$ and $(Me_3Si)_3P$ in a 2:1 mole ratio. Similarly, the dimer containing an In-P-In-P core, $[(Me_3SiCH_2)_2InP(SiMe_3)_2]_2$ (2) was prepared

by reaction in a 1:1 mole ratio. X-ray crystallographic analyses showed the In-P-In-Cl ring of 1 to be nonplanar while the In-P-In-P ring of 2 is planar. Compound 1 belongs to the triclinic system, space group $P \ 1 \ (C_i^l)$, with two molecules in a unit cell of dimensions: a=12.581(1), b=19.470(2), c=9.643(1) Å, $\alpha=89.75(1), \beta=112.91(1), \gamma=100.68(1)^\circ$. Compound 2 crystallizes in the orthorhombic system, space group $Pbcn(D_2h^{l4})$, with four molecules in a unit cell of dimensions: a=12.782(2), b=21.482(3), c=18.651(3) Å. Compound 2 reacts with two equivalents of (Me₃SiCH₂)₂InCl to yield 1 as a major product, as evidenced by 1 H and 13 C{ 1 H} NMR and melting point data.

Introduction

Recently, there has been heightened interest concerning the production of crystalline nanometer size particles (nanocrystals) of semiconductor materials, 1-4 because they possess the important feature of exhibiting quantum confinement effects not seen in the bulk material.5-8 Indeed, Alivisatos and coworkers recently reported the first proven example of the formation of nanocrystals of GaAs in polar organic solvents³ utilizing a dehalosilyation reaction [viz., GaCl₃ with (Me₃Si)₃As] reported by For some time, in our laboratory we have been applying this $us.^{9,10}$ dehalosilylation methodology to the syntheses novel III-V of compounds 11-17 for, in part, possible conversion to III-V materials. Thus. reaction between an organogroup III halide and a silvlarsine proceeds readily and, in a number of cases, the core fragments of these complexes are composed of four-membered rings containing two group III metals bridged by either two arsenic atoms, or by one arsenic and one halogen For example, compounds of the formula $R_2MAs(SiMe_3)_2M(R)_2Cl$ and atom. $[R_2MAs(SiMe_3)_2]_2$ (R = Ph^{13,14} or Me₃SiCH₂¹⁶, M = Ga; R = Me₃SiCH₂, ¹⁷ M = In) have been synthesized by us. In an effort to expand these fundamental investigations to include possible indium phosphide (InP) precursors, reactions were carried out with (Me₃SiCH₂)₂InCl and (Me₃Si)₃P. Herein, we report the isolation and crystal structure of the first example of In-P-In-Cl ring containing compound, a n (Me₃SiCH₂)₂InP(SiMe₃)₂In(CH₂SiMe₃)₂Cl (1), as well as the recently reported dimer $[(Me_3SiCH_2)_2InP(SiMe_3)_2]_2$ (2)⁴. The syntheses of compounds 1 and 2 from reactions of (Me₃SiCH₂)₂InCl and (Me₃Si)₃P in a

compounds 1 and 2 from reactions of (Me₃SiCH₂)₂InCl and (Me₃Si)₃P in a 2:1 and 1:1 mole ratio, respectively, are described. Additionally, the conversion of 2 to 1 is reported.

Experimental Section

General Considerations. All manipulations were performed using Schlenk techniques in a Vacuum/Atmospheres HE-43 Dri-Lab containing an argon atmosphere. Toluene was distilled from sodium/benzophenone ketyl under dry dinitrogen. Benzene-d6 was dried over sodium/benzophenone ketyl and vacuum transferred from the flask containing the latter. Hexane was distilled over LiAlH4 under dry dinitrogen. Indium(III) chloride was purchased from Alfa Products, Ward

Hill, MA and used as received. (Me₃Si)₃P was purchased from Quantum Design Inc., Austin, TX and was also used without further purification. (Me₃SiCH₂)₃In and (Me₂SiCH₂)₂InCl¹⁸ were prepared by literature ¹H, ³¹P and ¹³C NMR spectra were obtained on a Varian XL-300 (300.0, 121.4 and 75.4 MHz, respectively) spectrometer using 5 mm tubes. ¹H and ¹³C spectra were referenced to TMS using the residual protons or carbons of deuterated benzene at δ 7.15 ppm and δ 128 ppm, 31P spectra were referenced externally to H₃PO₄ at δ 0.00 respectively. NMR tubes were flame sealed under vacuum and all spectra were run in C₆D₆. All melting points were obtained from sealed capillaries with a Thomas-Hoover Uni-melt apparatus and are uncorrected. Crystals used in X-ray analyses were flame sealed under argon in 0.7 mm thin-walled glass capillaries. Elemental analyses were performed by E+R Microanalytical Laboratory, Inc., Corona, New York.

Preparation of $(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl(1)$.

In the dry box, $(Me_3SiCH_2)_2InCl$ (0.709 g, 2.18 mmol) in 15 mL of hexane and $(Me_3Si)_3P$ (0.273 g, 1.09 mmol) in 10 mL of hexane were combined in a 100-mL one-necked round-bottomed flask equipped with a Teflon valve and a micro-stirbar. After the resulting clear solution was removed from the box and stirred at room temperature for 24 h, the volatiles were removed in vacuo to yield a white residue. Dissolving the residue in approximately 3 mL of warm toluene followed by cooling to -15 °C for 5 days, afforded colorless crystals of 1 suitable for single-crystal X-ray analysis (0.657 g, 76% yield), m.p. 60-63 °C. Anal. Calcd (Found) for $C_{22}H_{62}CIIn_2PSi_6$: C, 33.30 (33.54); H, 8.01 (7.74); P, 3.91 (3.70). ¹H NMR: δ 0.16 (s, 8 H, CH_2), 0.26 (s, 36 H, $SiMe_3$), 0.33 (d, 18 H, $SiMe_3$) ($J_{P-H} = 5.6$

Hz)). ¹³C {¹H} NMR: δ 2.89 (s, SiMe₃), 4.62 [d, PSiMe₃ (J_{P-C} = 8.6 Hz)], 7.28 [d, CH₂ (J_{P-C} = 8.7 Hz)]. ³¹P {¹H} NMR: δ -218.99 (s)

Preparation of [(Me₃SiCH₂)₂InP(SiMe₃)₂]₂ (2). Reaction of (Me₃SiCH₂)₂InCl (0.628 g, 1.93 mmol) in 15 mL of hexane and (Me₃Si)₃P (0.484 g, 1.93 mmol) in 10 mL of hexane was carried out in a fashion analogous to that for 1. After stirring the resulting solution at room temperature for 24 h, the volatiles were removed in vacuo to yield a white The crude product was dissolved in approximately 20 mL of warm solid. toluene and, upon cooling the solution for 48 h at -15 °C, a multitude of clear, colorless, and extremely air-sensitive crystals of 2 suitable for single-crystal X-ray analysis resulted. Removal of approximately 80% of the toluene by evaporation afforded a second crop of 2 (0.767 g total, 85% yield) [mp 240 °C (lit⁴ mp 245 °C)]. Anal. Calcd (Found) for $C_{28}H_{80}In_2P_2Si_8$: C, 36.02 (36.23); H, 8.64 (8.21); P, 6.63 (6.42). ¹H NMR: δ 0.20 (s, 8 H, CH₂), 0.33 (s, 36 H, SiMe₃), 0.46 [t, 36 H, PSiMe₃ ($J_{P-H} = 2.4 \text{ Hz}$)]. ¹³C {¹H} NMR: δ 3.70 (s, SiMe₃), 4.11 (s, CH₂), 5.30 (t, PSiMe₃ (J_{P-C} = 4.2 Hz)). $^{31}P\{^{1}H\}$ NMR: δ -227.36 (s).

Reaction of 2 with (Me₃SiCH₂)₂InCl. (Me₃SiCH₂)₂InCl (12.5 mg, 0.038 mmol) and 2 (18.0 mg, 0.019 mmol) were combined in an NMR tube into which was vacuum distilled 0.75 mL of benzene-d₆. After freezing the contents of the tube with liquid dinitrogen, the tube was flame-sealed and allowed to warm to ambient temperature. Upon standing for 3 h, the ¹H NMR spectrum obtained for the mixture corresponded to that of an authentic sample of 1. The NMR tube was then opened in the dry box and the solvent evaporated to yield a colorless solid which melted at 63 °C, a mp comparable to that found for authentic 1, vide ante.

Structural Analyses of 1 and 2. Crystallographic data and measurements are presented in Table I. Intensity data were corrected for the usual Lorentz and polarization effects; empirical absorption corrections were also applied. The structure of 1 was solved by the heavy-atom Approximate coordinates for the indium atoms were derived from a Patterson map. The remaining non-hydrogen atoms were located in a series of weighted F_0 and difference Fourier syntheses. For 2, nonhydrogen atom coordinates of its isomorphous indium-arsenic analog¹⁷ were used as initial values. Positional and thermal parameters (at first isotropic, then anisotropic) for both compounds were adjusted by means of several rounds of full-matrix least-squares calculations. Hydrogen atoms, except for those at the somewhat disordered C(32') and C(33') methyl groups in 1, were included at their calculated positions during the final least-squares iterations which also included refinement of an extinction Structure-factor calculations, neutral atom scattering factors correction. and their anomalous dispersion corrections were taken from reference 19.

Results and Discussion

The ambient temperature reaction of (Me₃SiCH₂)₂InCl and (Me₃Si)₃P in a 2:1 mole ratio in hexane yields 1 via a dehalosilylation reaction (eq 1).

$$2(Me_3SiCH_2)_2InCl + (Me_3Si)_3P \longrightarrow$$

$$(Me3SiCH2)2InP(SiMe3)2In(CH2SiMe3)2Cl + Me3SiCl (1)$$

In that 1 contains an In-P-In-C1 ring, it is the first reported example of a compound with the two indium atoms being bridged by both a phosphorus atom and a chlorine atom, and is yet another example of what we refer to "mixed-bridge" complex/compound. 13-17 Compound 1 is the as complex phosphorus analog of recently reported our (Me₃SiCH₂)₂InAs(SiMe₃)₂In(CH₂SiMe₃)₂Cl(3) which, as indicated, contains both an arsenic and chlorine bridge. 17 Interestingly, 3 undergoes gradual decomposition at ambient temperature, whereas 1 is quite stable for extended periods of time.

Reaction of (Me₃SiCH₂)₂InCl with (Me₃Si)₃P in a 1:1 mole ratio afforded compound **2** (eq 2), the phosphorus analog of the dimer

$$(Me3SiCH2)2InCl + (Me3Si)3P \longrightarrow$$

$$1/2[(Me3SiCH2)2InP(SiMe3)2]2 + Me3SiCl (2)$$

$$2$$

[(Me₃SiCH₂)₂InAs(SiMe₃)₂]₂ (4)¹⁷. Dimer 2 contains an In-P-In-P core. Similarly, Theopold and coworkers also have isolated 2 and, while providing no detailed synthesis or complete structural characterization, it was reported that conversion of 2 to InP particles *via* an alcoholysis reaction was achieved.⁴

Previous studies in our laboratory have demonstrated quite clearly that dehalosilylation reactions between an organogallium or -indium halide and a silylarsine to form species containing metal-arsenic bonds occur

readily under mild conditions and in relatively high yields. $^{11-17}$ Although such reactions involving silylphosphines to form indium-phosphorus bonds have not been developed to the same extent, Barron and coworkers did report the isolation of InP from the thermolysis of the product obtained by the reaction of InX₃ (X = Cl, Br) with (Me₃Si)₃P and, similarly, used a dehalosilylation reaction to form (Me₂InPPh₂)₂. 20,21

The syntheses of 1 and 2 are clearly dependent upon the stoichiometry of the reagents used, and each is prepared in good yield. In the case of 1, this is in marked contrast to its arsenic analog (i.e., 3), since the latter mixed-bridge complex was produced in only 16% yield. Both 1 and 2 are very soluble in nonpolar organic solvents, but 2 is significantly less soluble than 1. Also, it is interesting to note that for the reactions involving (Me₃SiCH₂)₂GaCl with (Me₃Si)₃As in either a 1:1 or 2:1 mole ratio, only the mixed bridge compound was observed as the major product. ¹⁶ Additionally, compound 1 can be produced easily by the reaction of 2 with (Me₃SiCH₂)₂InCl in a 1:2 mole ratio (eq 3).

$$[(Me_3SiCH_2)_2InP(SiMe_3)_2]_2 + 2(Me_3SiCH_2)_2InCl \longrightarrow$$

$$2$$

$$(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl \qquad (3)$$

The ¹H NMR spectra of both 1 and 2 show there is coupling of the ³¹P nuclei with the methyl protons of the adjacent trimethylsilyl groups. The former exhibits a doublet while the latter a triplet. As Douglas and Theopold noted⁴, the triplet resonance for 2 reveals the dimeric nature of

the complex in solution. Thus, it would follow that complex 1 should exhibit a doublet being that there is only one phosphorus atom in the ring. It is from the inherent differences between the two ¹H NMR spectra that the conversion of 2 to 1 can be easily monitored from the reaction of 2 and additional (Me₃SiCH₂)₂InCl.

In the ¹³C NMR spectra, it is noteworthy that for both 1 and 2 coupling is again observed between the ³¹P nuclei and the adjacent trimethylsilyl groups. However, for complex 1, coupling is also seen with the adjacent methylene protons in the (trimethylsilyl)methyl groups. As for the ³¹P NMR spectra, of 1 and 2, each exhibits one sharp resonance indicating that each compound exist as a single species. This behavior for 2 differs substantially from that of [(Me₃SiCH₂)₂InPPh₂]₂ which was shown to exist as an equilibrium mixture of monomer and dimer in solution.²²

Crystals of 1 suitable for X-ray analysis were obtained by recrystallization from a toluene solution. Crystallographic data are summarized in Table I. Figure 1 presents an ORTEP diagram showing the atom numbering scheme for 1. Table II lists the non-hydrogen atoms fractional coordinates and equivalent isotropic thermal parameters; selected bond lengths and angles are reported in Table IV.

Compound 1 crystallizes in the triclinic system with the two molecules in the unit cell occupying the general positions of the centrosymmetric space group $P \ \overline{1}$. It is of interest that the In-P-In-Cl ring in 1 is distinctly non-planar, whereas in the As analog 3, the As and Cl atoms lie on a crystallographic C_2 symmetry axis and thus the

In-As-In-Cl ring is flat.¹⁷ The mean of the In-Cl bond lengths [2.630(3), 2.611(2) Å] at 2.621 Å in 1 is virtually identical to the In-Cl distance of 2.619(2) Å in 3. The Cl atom is displaced by 1.020 Å from the In-P-In' plane in 1 giving rise to a dihedral angle of 33.3(1)° between the In-P-In' and In-Cl-In' planes [mean endocylic torsion angle about the ring bonds = 22.9(1)°], and thus the ring is considerably puckered. The departure from coplanarity in 1 aids in relieving non-bonded intramolecular steric overcrowding of the bulky ring substituents. These effects are more severe in 1 than 3 as a consequence of the shorter distances for bonds involving phosphorus [mean In-P = 2.603 Å, mean P-Si = 2.252 Å] in contrast to the longer In-As and As-Si distances of 2.677(1) Å and 2.356(2) Å, respectively, in 3. The In-P-In', In-Cl-In' and mean P-In-Cl bond angles are 90.6(1), 89.8(1), and 85.1°, respectively.

Previous structural studies in our laboatory have shown that the Si-As-Si angle at $103.66(4)^\circ$ in $[(Me_3Si)_2AsGa(CH_2SiMe_3)_2]_2^{16}$ lies close to the essentially equal C-As-C angles of $104.3(2)^\circ$ subtended at the ring As atoms in $\{[(Me_3SiCH_2)_2As]_2GaBr\}_2^{12}$ and $104.4(2)^\circ$ in $[(Me_3SiCH_2)_2As-GaPh_2]_2$, thereby indicating that the Me₃Si and Me₃SiCH₂ ring substituents have comparable steric demands. The mean C-In-C bond angle at 127.9° in 1 is similar to the C-In-C angle of $126.3(3)^\circ$ in 3, and, although steric effects may make some contribution to the very significant enlargement over tetrahedral (109.5°) , the principal factors must be electronic in nature.

Recrystallization of 2 from toluene provided crystals suitab^{1,3} for an X-ray structural study. Crystal data are reported in Table 1 along with data collection and refinement parameters. An ORTEP diagram, with the

atom numbering scheme, is provided in Figure 2. Non-hydrogen atom fractional coordinates are listed in Table III; Table V contains selected bond lengths and angles.

Compound 2 crystallizes in the orthorhombic system, space group Pbcn, with four formula units per unit cell. It is isomorphous with $[(Me_3SiCH_2)_2InAs(SiMe_3)_2]_2$ (4)¹⁷ as well as $[(Me_3SiCH_2)_2GaAs(SiMe_3)_2]_2$,¹⁶ and thus accordingly it also lies on a crystallographic C_2 axis which passes through the group III centres. The four-membered ring is required by symmetry to be strictly planar. The In-P bonds [2.656(2), 2.654(2)] Å] are essentially equal and their mean at 2.655 Å is significantly greater (Δ = 0.051 Å) than the mean of 2.603 Å in 1; a similar difference of 0.045 Å, and in the same sense, is found between the In-As bonds of 3 and 4, indicating that group III-group V bond strain is greater in the dimers than in the mixed-bridged species. The bond angle pattern in the ring P-In-P << In-P-In (Δ = 7.2°) in 2 is also similar to that in the As analog 4 (Δ = 9.3°). The mean C-In-C angle at 123.2° in 2 is slightly smaller than that of 125.4° in 4; the Si-P-Si angles [105.2(2))° in 2, 105.4(2)° in 4] are equal.

The literature contains numerous examples of compounds containing In-P-In-P units. 2.4.21.22.24.25 However, only two such structures contain similar alkyl substituents (i.e., Me₃SiCH₂ or Me₃Si) and therefore warrant comparison with 2. As was previously noted, Beachley *et al* reported the structure of [(Me₃SiCH₂)₂InPPh₂]₂ (5).²² Compound 5 was prepared *via* two routes: an alkane elimination involving HPPh₂ and In(Me₃SiCH₂)₃ or a salt elimination between KPPh₂ and (Me₃SiCH₂)₂InBr. As found for 2, compound 5 contains a planar In-P-In-P core and the average In-P

length of 2.65(1) Å compares favorably to that of 2 (vide ante). Conversely, the mean In-P-In and P-In-P bond angles in 5 differ significantly from those in 2 [97.49(11) and 82.52(10)° for 5, and 93.6(1) and 86.4(1)° for 2, respectively]. These differences can be explained sterically where less demanding phenyl groups allow the In-P-In angle to open up somewhat. It then follows that with these smaller phenyl substituents, the Me₃SiCH₂ groups are able to move further apart, thus causing the P-In-P angle to decrease accordingly.

The only other published structural example of a compound containing an In-P-In-P ring with trimethylsilyl substituents on phosphorus was first reported in 1989 and then again in 1991 by Theopold and coworkers^{2,4} This compound, [Cp*(Cl)InP(SiMe₃)₂]₂ (6) (Cp* = C₅Me₅), is apparently produced by three different pathways: the novel reaction of Cp*₂InCl with LiP(SiMe₃)₂ to eliminate LiCp*₂, and by reaction of Cp*InCl₂ with either LiP(SiMe₃)₂ or P(SiMe₃)₃ to yield LiCl and Me₃SiCl, respectively⁴. Compound 6 has an average In-P bond length of 2.63(4) Å which is slightly shorter than those in 2, and it contains In-P-In and P-In-P bond angles [92.2(1) and 87.8(1)°, respectively] which are quite similar to those found in 2 (vide ante).

Conclusions

The work described here demonstrates that, in addition to being a facile route to compounds containing the In-P-In-P ring, the use of the dehalosilylation methodology allows for the ready preparation of the In-P-In-Cl moiety. As has been shown by Theopold and coworkers^{2,4},

organoindium compounds containing the (Me₃Si)₂P group can be converted to InP by alcoholysis and, in the case of 2, there is evidence for nanometer size particles being formed⁴. Thus, mixed-bridge complex 1 and some of its derivatives appear to be likely single-source InP precursors. In addition, the ease with which dimer 2 can be converted to the mixed bridge species 1, underscores the possible synthetic usefulness of this type of complex to the preparation of other related species. We will use this investigation as a another benchmark for future studies into the formation of suitable precursors to InP and other In containing III-V alloys.

Acknowledgment. The financial support for this work by the Office of Naval Research is gratefully acknowledged.

Supplementary Material Available: Tables of hydrogen atom coordinates and isotropic thermal parameters, anisotropic temperature factors, complete lists of interatomic distances and angles, including torsion angles for 1 and 2, and equations of least-squares planes through groups of atoms for 1 (13 pages); a listing of observed and calculated structure amplitudes for 1 and 2 (42 pages). Ordering information is given on any current masthead page.

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Captions to Figures

Figure 1. ORTEP diagram (40% probability ellipsoids) showing the structure and atom numbering scheme of $(Me_3SiCH_2)_2\overline{InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl} \quad (1); \quad hydrogen \quad atoms have been omitted for clarity.$

Figure 2. ORTEP diagram (40% probability ellipsoids) showing the structure and atom numbering scheme of $[(Me_3SiCH_2)_2InP(SiMe_3)_2]_2$ (2); hydrogen atoms have been omitted for clarity.

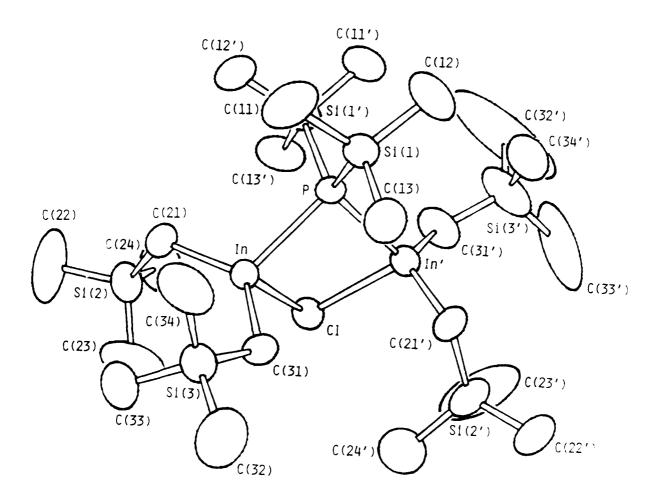


Figure 1

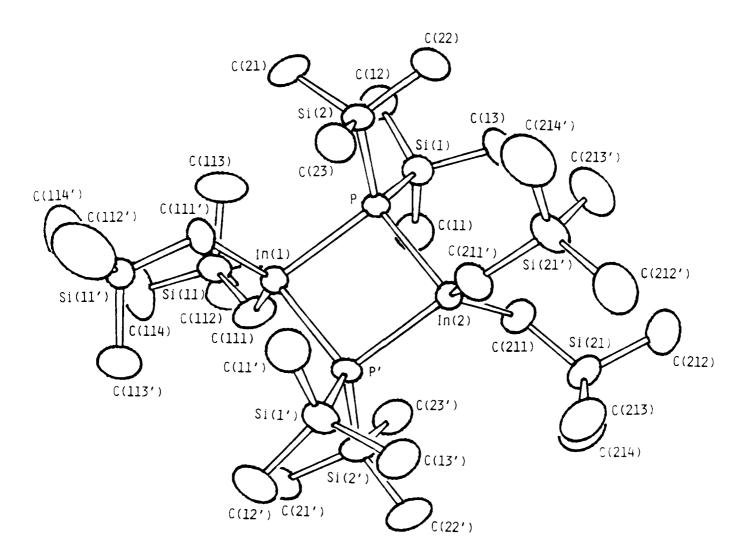


Figure 2

Table I. Crystallographic Data and Measurementsa for

 $(Me_3SiCH_2)_2InP(SiMe_3)_2In(CH_2SiMe_3)_2Cl \quad (1) \quad and \quad \\ [(Me_3SiCH_2)_2InP(SiMe_3)_2]_2 \quad (2)$

	1	2
molecular formula	C ₂₂ H ₆₂ PClIn ₂ Si ₆	C ₂₈ H ₈₀ P ₂ In ₂ Si ₈
formula weight	791.32	933.23
crystal system	triclinic	orthorhombic
space group	$P^{-1}(C_i^{-1})$	$Pbcn(D_{2h}^{14})$
a, Å	12.581(1)	12.782(2)
b, Å	19.470(2)	21.482(3)
c, Å	9.643(1)	18.651(3)
α, deg	89.75(1)	90.00(-)
β, deg	112.91(1)	90.00(-)
γ, deg	100.68(9)	90.00(-)
no. of orient. refls; θ, deg, range	25; 27-35	25; 35-40
V, Å ³	2132.1(9)	5121(2)
Z	2	4
D _{calcd} , g cm ⁻³	1.233	1.210
temp, °C	23	23
crystal dimensions, mm	0.14 x 0.19 x 0.45	0.32 x 0.40 x 0.44
T _{max} :T _{min}	1.00:0.55	1.00:0.46
radiation (wavelength)	Cu-Kα (1.5418 Å)	Cu-Kα (1.5418 Å)
μ. cm-1	115.2	99.2
scan type	ω-2θ	ω-2θ

Table I. (continued)

scan width, deg	$0.80 + 0.14 \tan\theta$	$0.80 + 0.14 \tan\theta$
θ_{max} , deg	65	7 5
intensity control reflns	222,312,151,141	115,223,223,115
variation; repeat time, h	<2%; 2	<1%; 2
no of rflns recorded	8061 (+ <i>h</i> , <u>+</u> <i>k</i> , <u>+</u> <i>l</i>)	5261 (+h,+k,+l)
no of rflns retained, $I > 3.0\sigma(I)$	4077	2081
no of parameters refined	290	183
extinction correction	$6.6(5) \times 10^{-7}$	$2.8(1) \times 10^{-7}$
R, R_w^b	0.046, 0.058	0.047, 0.062
goodness-of-fit ^c	1.16	1.15
max shift; esd in final least-squares cycle	0.02	0.02
final $\Delta \rho(e/Å^3)$ max; min	0.82; -0.58	0.79; -1.12

^aAn Enraf-Nonius CAD-4 diffractometer equipped with a graphite monochromater was used for all measurements. Crystallographic calculations were performed on PDP11/44 and MicroVAX computers by use of the Enraf-Nonius Structure Determination Package (SDP).

 ${}^bR = \Sigma ||F_0| - |F_c||/\Sigma ||F_0||; R_w = [\Sigma w (|F_0| - |F_c|)^2/\Sigma w ||F_0|^2]^{1/2}; \Sigma w \Delta^2 [w = 1/\sigma^2(|F_0|), \Delta = (|F_0| - |F_c|)]$ was minimized.

^cGoodness-of-fit = $[\Sigma w \Delta^2 / (N_{\text{observations}} - N_{\text{parameters}})]^{1/2}$.

Table II. Non-hydrogen Atom Fractional Coordinates and Equivalent Isotropic Thermal Parameters for 1, with Estimated Standard Deviations in Parentheses.

atom	x	y	Z	$B_{eq}(Å^2)$
P	0.0584(2)	0.3070(1)	0.3304(2)	3.92(4)
In	-0.11679(4)	0.20821(3)	0.16724(6)	4.15(1)
In'	0.19445(4)	0.26442(3)	0.21818(6)	4.47(1)
a	-0.0007(2)	0.2094(1)	-0.0084(2)	5.04(5)
Si(1)	0.1128(2)	0.3083(1)	0.5825(3)	4.83(6)
Si(2)	-0.3588(2)	0.2204(2)	-0.1570(3)	6.81(8)
Si(3)	-0.2105(2)	0.0633(2)	0.3245(3)	6.36(7)
Si(1')	0.0193(2)	0.4111(1)	0.2456(3)	5.75(7)
Si(2')	0.2914(3)	0.1105(2)	0.2264(3)	7.89(8)
Si(3')	0.4265(3)	0.3903(3)	0.2248(4)	13.1(1)
C(11)	-0.0083(9)	0.3288(7)	0.6312(11)	9.5(3)
C(12)	0.2509(10)	0.3762(7)	0.6785(12)	8.9(4)
C(13)	0.1390(9)	0.2204(5)	0.6403(10)	6.7(3)
C(11')	0.1511(10)	0.4826(5)	0.3324(13)	8.1(4)
C(12')	-0.1017(9)	0.4329(6)	0.2911(14)	8.8(4)
C(13')	-0.0270(11)	0.4027(5)	0.0352(12)	8.4(4)
$\mathbb{C}(21)$	-0.2749(7)	0.2476(5)	0.0485(9)	5.4(2)
C(22)	-0.5130(11)	0.2282(13)	-0.2145(15)	16.8(7)
$\mathbb{C}(23)$	-0.3598(17)	0.1286(8)	-0.2013(16)	14.2(7)
C(24)	-0.2956(11)	0.2733(8)	-0.2742(13)	10.6(5)
C(31)	-0.0993(7)	0.1067(4)	0.2547(9)	5.1(2)
C(32)	-0.1781(11)	-0.0234(7)	0.3926(16)	12.3(4)
C(33)	-0.3602(9)	0.0426(7)	0.1638(15)	9.3(4)
C(34)	-0.2183(11)	0.1196(8)	0.4709(14)	12.5(4)
C(21')	0.2608(7)	0.1768(5)	0.3336(10)	6.0(2)
C(22')	0.4006(9)	0.0631(6)	0.3554(14)	9.3(4)
C(23')	0.3289(14)	0.1453(9)	0.0734(15)	19.9(5)

Table II. (continued)

atom	x	y	z	$B_{\rm eq}({\rm \AA}^2)$
C(24')	0.1528(15)	0.0437(9)	0.1306(20)	18.7(6)
C(31')	0.2801(8)	0.3410(6)	0.1140(10)	8.0(3)
C(32')	0.4452(22)	0.4814(12)	0.1737(23)	40.5(8)
C(33')	0.5314(13)	0.3414(16)	0.2033(25)	48(1)
C(34')	0.4576(12)	0.3963(8)	0.4283(17)	11.5(5)

Table III. Non-hydrogen Atom Fractional Coordinates and Equivalent Isotropic Thermal Parameters for 2, with Estimated Standard Deviations in Parentheses.

atom	X	у	Z	$B_{\rm eq}({\rm \AA}^2)$
P	0.1411(2)	0.1854(1)	0.2382(1)	3.01(4)
In(1)	$0.0000(-)^a$	0.27559(3)	0.2500(-)a	3.23(1)
In(2)	$0.0000(-)^a$	0.09537(3)	0.2500(-)a	3.04(1)
Si(1)	0.2355(2)	0.1746(1)	0.1368(2)	4.47(6)
Si(2)	0.2589(2)	0.1895(2)	0.3280(2)	4.53(6)
Si(11)	0.0388(3)	0.3885(1)	0.1151(2)	4.45(6)
Si(21)	-0.0846(3)	-0.0219(1)	0.1310(2)	5.20(7)
C(11)	0.1468(12)	0.1906(6)	0.0608(6)	6.3(3)
C(12)	0.3503(10)	0.2281(6)	0.1338(8)	7.0(3)
C(13)	0.2859(10)	0.0928(6)	0.1295(7)	6.3(3)
C(21)	0.3309(10)	0.2656(6)	0.3285(8)	7.3(4)
C(22)	0.3581(10)	0.1257(6)	0.3195(7)	6.8(3)
C(23)	0.1871(10)	0.1812(6)	0.4157(6)	6.2(3)
C(111)	-0.0392(10)	0.3241(5)	0.1513(6)	5.7(3)
C(112)	0.0290(16)	0.3892(10)	0.0162(10)	14.8(8)
C(113)	0.1804(12)	0.3845(8)	0.1387(11)	10.6(5)
C(114)	-0.0162(19)	0.4620(6)	0.1416(16)	16.7(9)
C(211)	-0.0028(10)	0.0476(4)	0.1472(16)	4.6(2)
C(212)	-0.0011(13)	-0.0911(6)	-0.1090(11)	9.7(5)
C(213)	-0.1740(12)	-0.0407(6)	0.2065(8)	8.1(4)
C(214)	-0.1701(13)	-0.0114(8)	0.0523(9)	9.3(5)

a Fixed by symmetry.

Table IV. Selected Bond Distances (Å) and Angles (deg) for 1, with Estimated Standard Deviations in Parentheses.

	D.	and Lanatha		
D. I.		ond Lengths	0 (11(0)	
P-In	2.605(2)	In'-Cl	2.611(2)	
P-In'	2.601(3)	In-C(21)	2.15(1)	
P-Si(1)	2.253(3)	In'-C(21')	2.15(1)	
P-Si(1')	2.250(3)	In-C(31)	2.16(1)	
In-Cl	2.630(3)	In'-C(31')	2.15(1)	
	В	ond Angles		
In-P-In'	90.6(1)	Cl-In-C	(31)	99.5(3)
In-P-Si(1)	116.8(1)	Cl-In'-C	(31')	102.4(2)
In-P-Si(1')	108.8(1)	C(21)-Ir	a-C(31)	128.8(3)
In'-P-Si(1)	117.7(1)	C(21')-I	n'-C(31')	126.9(4)
In'-P-Si(1')	110.2(1)	In-Cl-In	ı '	89.8(1)
Si(1)-P-Si(1')	111.1(1)	P-Si(1)-	C(11)	109.2(3)
P-In-Cl	84.9(1)	P-Si(1')	-C(11')	111.2(3)
P-In'-Cl	85.3(1)	P-Si(1)-	C(12)	109.6(4)
P-In-C(21)	112.2(2)	P-Si(1')-	·C(12')	110.5(4)
P-In'-C(21')	110.1(3)	P-Si(1)-	C(13)	107.8(3)
P-In-C(31)	112.2(2)	P-Si(1')-	-C(13')	106.9(3)
P-In'-C(31')	116.6(3)	In-C(21)		118.3(5)
Cl-In-C(21)	108.7(3)	In-C(21'		118.1(5)
Cl-In'-C(21')	105.3(2)	In-C(31		117.5(5)
	•	, 2 3	· · · · · ·	

Table V. Selected Bond Distances (Å) and Angles (deg) for 2, with Estimated Standard Deviations in Parentheses.

	Bond	Lengths	
P-In(1)	2.656(2)	In(1)-C(111)	2.174(11)
P-In(2)	2.654(2)	In(2)-C(211)	2.175(9)
P-Si(1)	2.255(4)		
P-Si(2)	2.254(4)		
	Bond	Angles	
In(1)-P-In(2)	93.6(1)	P-Si(2)-C(22)	111.1(4)
In(1)-P-Si(1)	120.5(1)	P-Si(2)-C(23)	108.4(4)
In(1)-P-Si(2)	111.3(1)	P-In(1)-C(111')	105.3(3)
In(2)-P-Si(1)	111.0(1)	P-In(1)-(P')	86.3(1)
In(2)-P-Si(2)	114.8(1)	C(111)-In(1)-C(11)	11') 122.7(4)
Si(1)-P-Si(2)	105.7(2)	P-In(2)-C(211)	106.4(3)
P-In(1)-C(111)	115.9(3)	P-In(2)-P'	86.4(1)
P-Si(1)-C(11)	107.2(5)	P-In(2)-C(211')	113.9(3)
P-Si(1)-C(12)	112.5(5)	C(211)-In(2)-C(2	11') 123.7(3
P-Si(1)-C(13)	109.9(4)	In(1)-C(111)-Si(1	1) 123.2(6
P-Si(2)-C(21)	111.4(5)	In(2)-C(211)-Si(2	1) 122.3(5

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